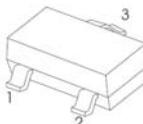


SOT-23 Plastic-Encapsulate MOSFETS

SI2302 N-Channel 20-V(D-S) MOSFET

V_{(BR)DSS}	R_{DS(on)MAX}	I_D	SOT-23
20V	80mΩ@4.5V	2.0A	
	115mΩ@2.5V		

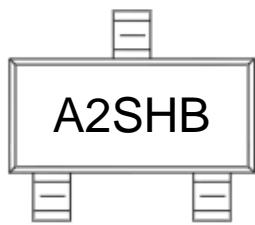
FEATURE

- TrenchFET Power MOSFET

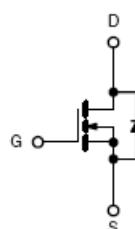
APPLICATION

- Load Switch for Portable Devices
- DC/DC Converter

MARKING



Equivalent Circuit



Maximum ratings ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	20	V
Gate-Source Voltage	V _{GS}	±8	
Continuous Drain Current	I _D	2.0	A
Continuous Source-Drain Current(Diode Conduction)	I _S	0.6	
Power Dissipation	P _D	0.4	W
Thermal Resistance from Junction to Ambient ($t \leq 5\text{s}$)	R _{θJA}	312.5	°C/W
Operating Junction	T _J	150	°C
Storage Temperature	T _{STG}	-55 ~ +150	

MOSFET ELECTRICAL CHARACTERISTICS

$T_a=25^{\circ}\text{C}$ unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Static						
Drain-source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_D = 10\mu\text{A}$	20			V
Gate-threshold voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = 50\mu\text{A}$	0.65	0.95	1.2	
Gate-body leakage	I_{GSS}	$V_{\text{DS}} = 0\text{V}, V_{\text{GS}} = \pm 8\text{V}$			± 100	nA
Zero gate voltage drain current	I_{DSS}	$V_{\text{DS}} = 20\text{V}, V_{\text{GS}} = 0\text{V}$			1	μA
Drain-source on-resistance ^a	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = 4.5\text{V}, I_D = 3.6\text{A}$		0.050	0.080	Ω
		$V_{\text{GS}} = 2.5\text{V}, I_D = 3.1\text{A}$		0.080	0.115	
Forward transconductance ^a	g_{fs}	$V_{\text{DS}} = 5\text{V}, I_D = 3.6\text{A}$		8		S
Diode forward voltage	V_{SD}	$I_S = 0.94\text{A}, V_{\text{GS}} = 0\text{V}$		0.76	1.2	V
Dynamic						
Total gate charge	Q_g	$V_{\text{DS}} = 10\text{V}, V_{\text{GS}} = 4.5\text{V}, I_D = 3.6\text{A}$		4.0	10	nC
Gate-source charge	Q_{gs}			0.65		
Gate-drain charge	Q_{gd}			1.5		
Input capacitance ^b	C_{iss}	$V_{\text{DS}} = 10\text{V}, V_{\text{GS}} = 0\text{V}, f = 1\text{MHz}$		300		pF
Output capacitance ^b	C_{oss}			120		
Reverse transfer capacitance ^b	C_{rss}			80		
Switching^b						
Turn-on delay time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}} = 10\text{V}, R_L = 5.5\Omega, I_D \approx 3.6\text{A}, V_{\text{GEN}} = 4.5\text{V}, R_g = 6\Omega$		7	15	ns
Rise time	t_r			55	80	
Turn-off delay time	$t_{\text{d}(\text{off})}$			16	60	
Fall time	t_f			10	25	

Notes :

- a. Pulse Test : Pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
- b. These parameters have no way to verify.